

**Amendments to the Specification**

Please amend the last paragraph on page 2 of the specification as follows:

--The present invention relates to a method for recycling a substrate. The substrate has a ~~residue on its surface and a~~ detachment profile that includes a residue or residual topography resulting from an ion implantation process. The method includes the steps removing the residue from the substrate to a level substantially equivalent to that of the detachment profile to obtain a substantially uniform planar surface on the substrate; and polishing the entire surface of the substrate to eliminate defects and to prepare the surface in condition for molecular bonding to another substrate.--

Please amend the 3<sup>rd</sup> paragraph on page 3 of the specification as follows:

--The residue can also be removed using a local ion attack. The residue can be bombarded with at least one of ions and ion clusters to sever the residue. For example, an ion beam can be directed approximately perpendicular to the surface of the substrate to remove the residue. An Argon ion beam is suitable for this purpose. A laser beam can also be used to sever the residue. This is generally focused on at least the interface, such as by being aligned parallel to the surface of the substrate. If desired, the laser beam can be focussed onto the residue ~~swing~~ using a screen having a slit.--